

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH3481 — Low Votage Drive Switching Device Applications

Features

- ON-resistance R_{DS}(on)1=80m Ω (typ.)
- · Halogen free compliance

- 1.2V drive
- · Protection diode in

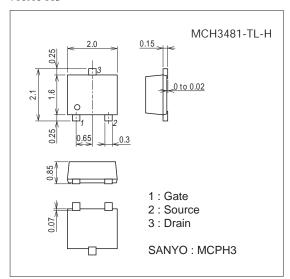
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	VGSS		±9	V
Drain Current (DC)	ID		2	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7019A-003

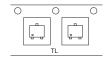


Product & Package Information

Package : MCPH3JEITA, JEDEC : SC-70, SOT-323

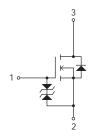
• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL Marking





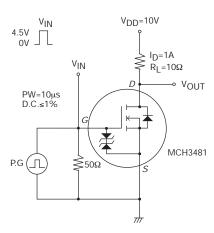
Electrical Connection



Electrical Characteristics at Ta=25°C

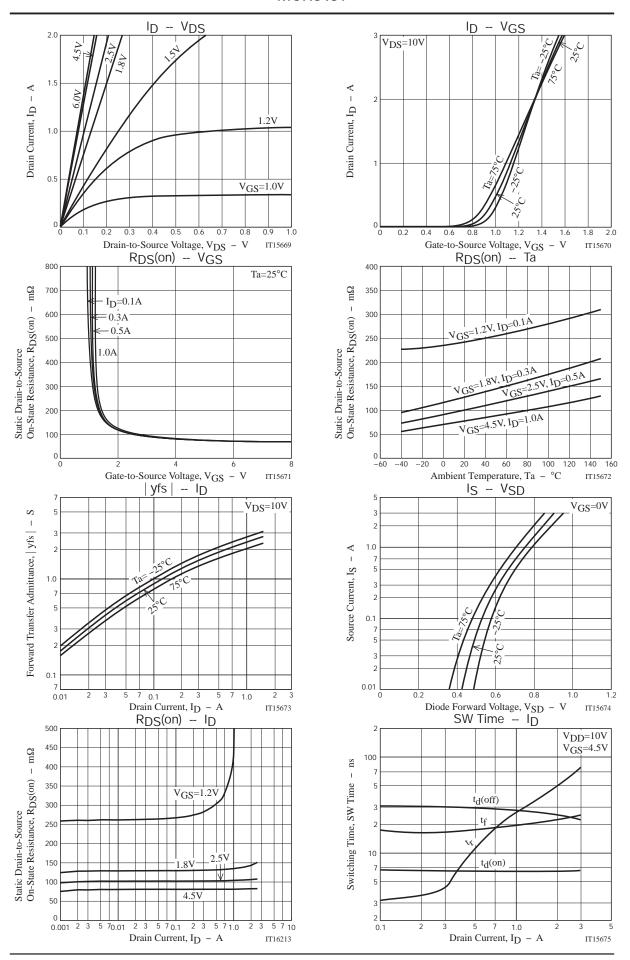
Parameter	Cumala al	O and Millians	Ratings			1.114	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±7.2V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.3		0.9	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1A		2.4		S	
	R _{DS} (on)1	I _D =1A, V _G S=4.5V		80	104	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =0.5A, V _G S=2.5V		105	147	mΩ	
Static Dialit-to-Source Off-State Resistance	RDS(on)3	ID=0.3A, VGS=1.8V		135	203	mΩ	
	R _{DS} (on)4	I _D =0.1A, V _{GS} =1.2V		270	540	mΩ	
Input Capacitance	Ciss			175		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		30		pF	
Reverse Transfer Capacitance	Crss			25		pF	
Turn-ON Delay Time	t _d (on)			6.6		ns	
Rise Time	t _r	Can amonified Took Circuit		27		ns	
Turn-OFF Delay Time t _d (off)		See specified Test Circuit.		28		ns	
Fall Time	t _f	1		19		ns	
Total Gate Charge	Qg			2.9		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.46		nC	
Gate-to-Drain "Miller" Charge Qgd		1		0.53		nC	
Diode Forward Voltage	VSD	IS=2A, VGS=0V		0.85	1.2	V	

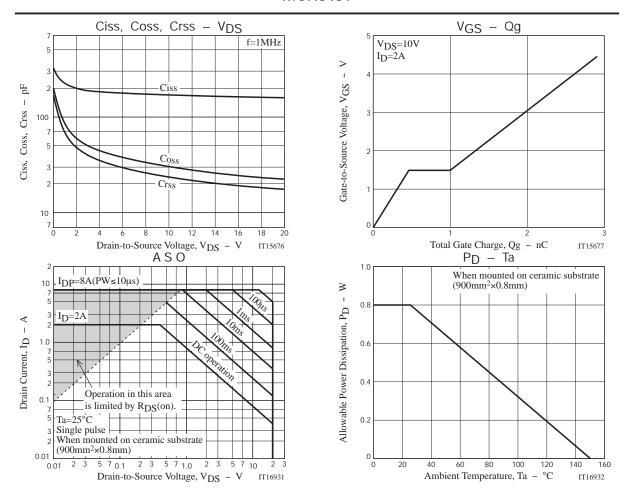
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo		
MCH3481-TL-H	MCPH3	3.000pcs./reel	Pb Free and Halogen Free		



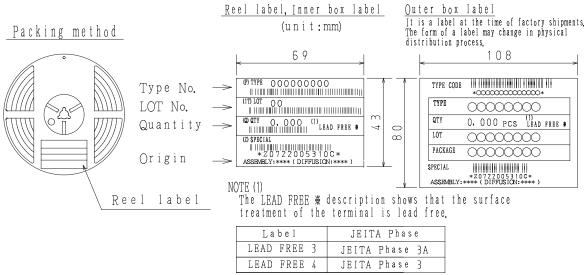


Taping Specification

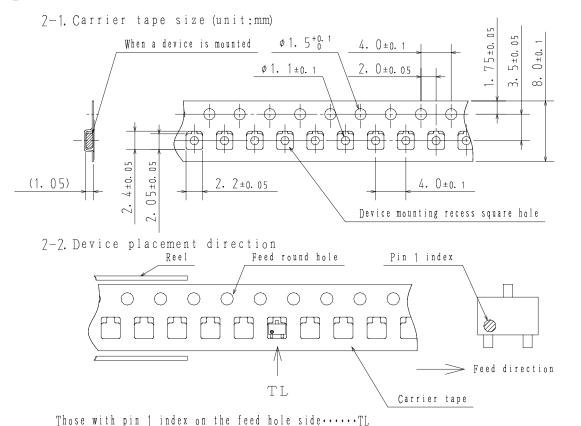
MCH3481-TL-H

1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
мсрн3	мсрн3	3, 000	15,000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	

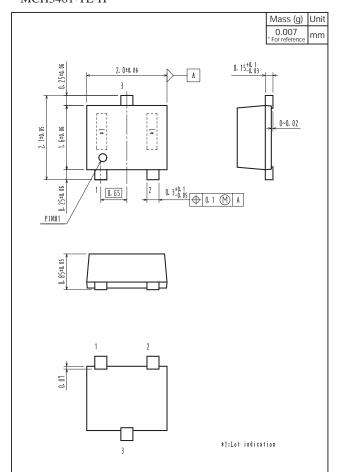


2. Taping configuration

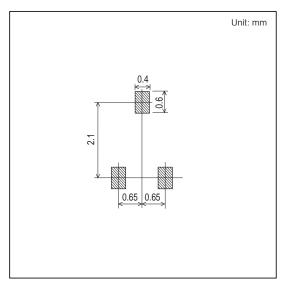


Outline Drawing

MCH3481-TL-H



Land Pattern Example



Note on usage: Since the MCH3481 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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